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Commission Crystal Growth and Characterization of Materials, International Union of Crystallography support the application of Polish Society of Crystal Growth to Polish Parliament to establish a year 2013 "The year dedicated to prof. Jan Czochralski".

In 1916 professor Jan Czochralski invented a method for measuring of the crystallization velocity of metals. The idea of this method was based on pulling of a fiber of different metals from their melts. The obtained metallic wires proved to be single crystals.

The results of the Czochralski studies were published in several papers. The first one was published in Zeitschrift für Physikalische Chemie in 1918. This new technique allowed him to obtain the good quality single crystals of pure metals like Sn, Pb, Zn. When transistor was invented, the Czochralski pulling method was adopted by the Americans G.K. Teal and J.B. Little from Bell Telephone Laboratory for growing large single crystals of semiconductors on an industrial scale. Initially, germanium and silicon were grown, but later other semiconductors, oxides, fluorides and different binary and multicomponents compounds were also obtained as single crystals by the Czochralski method.



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IMEM-CNR

and

Chair, Commission Crystal Growth and Characterization of Materials,
International Union of Crystallography